



4-Mbit (256K words × 16-bit) Static RAM with Error-Correcting Code (ECC)

Features

- AEC-Q100 qualified
- High speed□ t_{AA} = 10 ns
- Temperature range
 - □ Automotive-E: -40 °C to 125 °C
 - □ Automotive-A: -40 °C to 85 °C
- Embedded ECC for single-bit error correction^[1, 2]
- Low active and standby currents
 - ☐ Active current I_{CC} = 40 mA typical
 - ☐ Standby current I_{SB2} = 6 mA typical
- Operating voltage range: 2.2 V to 3.6 V
- 1.0 V data retention
- TTL- compatible inputs and outputs
- Pb-free 48-ball VFBGA and 44-pin TSOP II packages

Functional Description

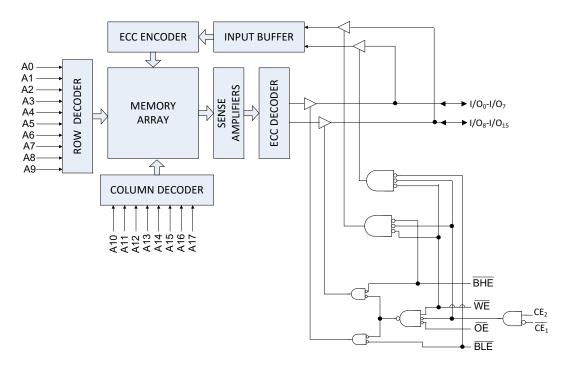
CY7C1041G is a high-performance CMOS fast static RAM automotive part with embedded ECC. This device has a single Chip Enable (CE) input and is accessed by asserting it LOW.

Data writes are performed by asserting the Write Enable ($\overline{\text{WE}}$) input LOW, while providing the data on I/O₀ through I/O₁₅ and the address on A₀ through A₁₇ pins. The Byte High Enable (BHE) and Byte Low Enable (BLE) inputs control write operations to the upper and lower bytes of the specified memory location. BHE controls I/O₈ through I/O₁₅ and BLE controls I/O₀ through I/O₇.

Data reads are performed by asserting the Output Enable (\overline{OE}) input and providing the required address on the address lines. Read data is accessible on the I/O lines (I/O $_0$ through I/O $_1$ 5). Byte accesses <u>can</u> be <u>performed</u> by asserting the required byte enable signal (BHE or BLE) to read either the upper byte or the lower byte of data from the specified address location.

All I/Os (I/O $_0$ through $\underline{I/O}_{15}$) are placed in a HI-Z state when the device is deselected ($\overline{\text{CE}}$ LOW), or when the control signals are deasserted ($\overline{\text{OE}}$, $\overline{\text{BLE}}$, $\overline{\text{BHE}}$). Refer to the following logic block diagram.

Logic Block Diagram - CY7C1041G



Note

- 1. This device does not support automatic write-back on error detection.
- 2. SER FIT Rate < 0.1 FIT/Mb. Refer AN88889 for details.

CY7C1041G Automotive



Contents

Pin Configurations	3
Product Portfolio	
Maximum Ratings	
Operating Range	
DC Electrical Characteristics	
Capacitance	5
Thermal Resistance	5
AC Test Loads and Waveforms	5
Data Retention Characteristics	
Data Retention Waveform	
AC Switching Characteristics	
Switching Waveforms	
Truth Table	

Ordering information	
Ordering Code Definitions	12
Package Diagrams	13
Acronyms	14
Document Conventions	14
Units of Measure	14
Document History Page	15
Sales, Solutions, and Legal Information	16
Worldwide Sales and Design Support	16
Products	16
PSoC® Solutions	16
Cypress Developer Community	16
Technical Support	

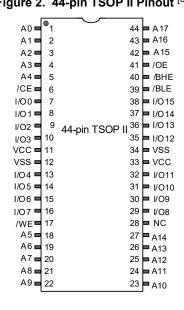


Pin Configurations

Figure 1. 48-ball VFBGA Pinout [3]

1	2	3	4	5	6	_
BLE	(OE)	\bigcirc A ₀	\bigcirc A ₁	\bigcirc A ₂	NC	А
(I/O ₈)	BHE	\bigcirc A ₃	\bigcirc A ₄ $)$	(CE)	(I/O ₀)	В
(I/O ₉)	(I/O ₁₀)	$\left(A_{5}\right)$	${\color{red} \bigcirc} {\color{blue} A_6}$	(I/O ₁)	(I/O ₂)	С
vss	(I/O ₁₁)	(A ₁₇)	\bigcirc A ₇	(I/O ₃)	vcc	D
vcc	(I/O ₁₂)	$\widehat{\rm NC})$	(A ₁₆)	(I/O ₄)	vss	Е
(I/O ₁₄)	(I/O ₁₃)	$\left(A_{14} \right)$	(A ₁₅)	(I/O ₅)	(I/O ₆)	F
(I/O ₁₅)	$\widehat{\rm NC}$	$\left(A_{12}\right)$	$\left(A_{13}\right)$	$\widehat{\overline{\text{WE}}}$	(I/O ₇)	G
NC	${\color{red} {\color{red} A_8}}$	${\color{red} {\color{red} A_9}}$	$\left(A_{10} \right)$	$\left(A_{11} \right)$	NC	Н
						J

Figure 2. 44-pin TSOP II Pinout [3]



Product Portfolio

				Power Dissipation				
Product	Range V _{CC} Range (V)		Speed (ns)	Operating I _{CC} , (mA), f = f _{max}		Standby, I _{SB2} (mA)		
			()	Typ ^[4]	Max	Typ ^[4]	Max	
CY7C1041G	Automotive-E	2.2 V-3.6 V	10	40	50	6	14	
	Automotive-A			38	45	6	8	

- 3. NC pins are not connected internally to the die.
- 4. Typical values are included for reference only and are not guaranteed or tested.



Maximum Ratings

DC input voltage ^[5]	0.3 V to V _{CC} + 0.3 V
Current into outputs (in low state)	20 mA
Static discharge voltage (MIL-STD-883, Method 3015)	> 2001 V
Latch-up current	> 140 mA

Operating Range

Grade	Ambient Temperature	V _{cc}		
Automotive-E	–40 °C to +125 °C	2.2 V to 3.6 V		
Automotive-A	–40 °C to +85 °C	2.2 V to 3.6 V		

DC Electrical Characteristics

Over the Operating Range

Parameter	Description		Test Conditions	10 ns (Automotive-E)			10 ns (Automotive-A)			Unit	
Parameter	Des	cription	Test C	onaitions	Min	Тур	Max	Min	Тур	Max	Oint
V _{OH}	Output	2.2 V to 2.7 V	V _{CC} = Min, I _C	_{DH} = -1.0 mA	2	-	_	2	_	_	V
	HIGH voltage	2.7 V to 3.0 V	V _{CC} = Min, I _C	_{DH} = -4.0 mA	2.2	_	_	2.2	_	_	
	Voltage	3.0 V to 3.6 V	V _{CC} = Min, I _C	$V_{\rm CC}$ = Min, $I_{\rm OH}$ = -4.0 mA $= 2$		_	_	2.4	_	_	
V _{OL}	Output	2.2 V to 2.7 V	V _{CC} = Min, I _C	_{DL} = 2 mA	_	_	0.4	_	_	0.4	V
	LOW voltage	2.7 V to 3.6 V	V _{CC} = Min, I _C	_{DL} = 8 mA	_	-	0.4	_	_	0.4	
V _{IH}		2.2 V to 2.7 V	_		2	_	$V_{CC} + 0.3^{[5]}$	2	_	$V_{CC} + 0.3^{[5]}$	V
	voltage	2.7 V to 3.6 V	_		2	_	$V_{CC} + 0.3^{[5]}$	2	_	$V_{CC} + 0.3^{[5]}$	
V _{IL}	Input LOW	2.2 V to 2.7 V	-		-0.3 ^[5]	-	0.6	$-0.3^{[5]}$	_	0.6	V
	voltage	2.7 V to 3.6 V	-		-0.3 ^[5]	-	0.8	$-0.3^{[5]}$	_	0.8	
I _{IX}	Input leakag	ge current	GND ≤ V _{IN} ≤ V _{CC}		- 5	_	+5	-1	_	+1	μА
I _{OZ}	Output leak	age current	rrent GND ≤ V _{OUT} ≤ V _{CC} , Output disabled		– 5	-	+5	-1	-	+1	μА
Icc	Operating s	upply current	V _{CC} = 3.6 V, I _{OUT} = 0 mA, CMOS levels	$f = f_{MAX} = 1/t_{RC}$	-	40	50	-	38	45	mA
I _{SB1}	Automatic C current – T	CE power down TL inputs	$V_{CC} = 3.6 \text{ V},$ $V_{IN} \ge V_{IH} \text{ or } V_{IM}$ $f = f_{MAX}$		_	Ι	24	-	-	15	mA
I _{SB2}	Automatic C current – Cl	CE power down MOS inputs	$V_{CC} = 3.6 \text{ V},$ $\overline{CE} \ge V_{CC} - 0$ $V_{IN} \ge V_{CC} - 0$ $V_{IN} \le 0.2 \text{ V},$ $f = 0$		-	6	14	-	6	8	mA

Note

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^{5.} $V_{IL(min)} = -2.0 \text{ V}$ and $V_{IH(max)} = V_{CC} + 2 \text{ V}$ for pulse durations of less than 20 ns.



Capacitance

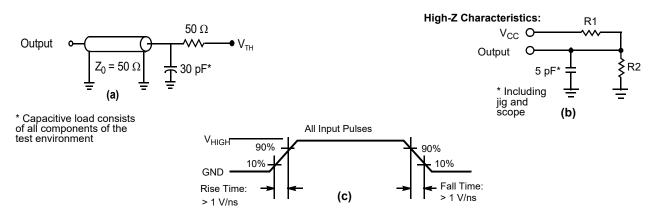
Parameter ^[6]	Description	Test Conditions	All Packages	Unit
C _{IN}	Input capacitance	$T_A = 25 ^{\circ}\text{C}$, $f = 1 \text{MHz}$, $V_{CC} = V_{CC(typ)}$	10	pF
C _{OUT}	I/O capacitance		10	pF

Thermal Resistance

Parameter ^[6]	Description	Test Conditions	48-ball VFBGA	44-pin TSOPII	Unit
$\Theta_{\sf JA}$		Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	30.68	66.82	°C/W
$\Theta_{\sf JC}$	Thermal resistance (junction to case)		14.83	15.97	°C/W

AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms [7]



Parameters	3.0 V	Unit
R1	317	Ω
R2	351	Ω
V _{TH}	1.5	V
V _{HIGH}	3	V

- 6. Tested initially and after any design or process change that may affect these parameters.
 7. Full-device AC operation assumes a 100 μs ramp time from 0 to V_{CC(min)} and a 100 μs wait time after V_{CC} stabilization.



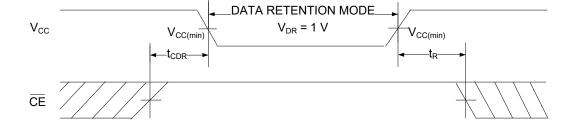
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Automotive-E		Automotive-A		11:0:4
	Description	Conditions	Min	Max	Min	Max	Unit
V_{DR}	V _{CC} for data retention	_	1	_	1	_	V
I _{CCDR}	Data retention current	V _{CC} = 1.2 V,	_	14	_	8	mA
		$V_{CC} = 1.2 \text{ V},$ $\overline{CE} \ge V_{CC} - 0.2 \text{ V},$					
		$V_{IN} \ge V_{CC} - 0.2 \text{ V or}$ $V_{IN} \le 0.2 \text{ V}$					
t _{CDR} ^[8]	Chip deselect to data retention time	-	0	_	0	_	ns
t _R ^[8, 9]	Operation recovery time	V _{CC} ≥ 2.2 V	10	-	10	_	ns

Data Retention Waveform

Figure 4. Data Retention Waveform [9]



^{8.} These parameters are guaranteed by design.
9. Full-device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min.)} ≥ 100 μs or stable at V_{CC(min.)} ≥ 100 μs.



AC Switching Characteristics

Over the Operating Range

D[10]	D	10 ns (Automotive	10 ns (Automotive-A/Automotive-E)			
Parameter ^[10]	Description	Min	Max	Unit		
Read Cycle		-				
t _{RC}	Read cycle time	10	_	ns		
t _{AA}	Address to data	-	10	ns		
t _{OHA}	Data	3	_	ns		
t _{ACE}	CE LOW to data ^[11]	-	10	ns		
t _{DOE}	OE LOW to data	-	4.5	ns		
t _{LZOE}	OE LOW to low impedance ^[12, 13]	0	_	ns		
t _{HZOE}	OE HIGH to HI-Z ^[12, 13]	-	5	ns		
t _{LZCE}	CE LOW to low impedance ^[11, 12, 13]	3	_	ns		
t _{HZCE}	CE HIGH to HI-Z ^[11, 12, 13]	-	5	ns		
t _{PU}	CE LOW to power up ^[11, 13]	0	_	ns		
t _{PD}	CE HIGH to power down ^[11, 13]	-	10	ns		
t _{DBE}	Byte enable to data valid	-	4.5	ns		
t _{LZBE}	Byte enable to low impedance ^[13]	0	_	ns		
t _{HZBE}	Byte disable to HI-Z ^[13]	-	6	ns		
Write Cycle ^{[14}	i, 15]	<u>.</u>		•		
t _{WC}	Write cycle time	10	_	ns		
t _{SCE}	CE LOW to write end ^[10]	7	_	ns		
t _{AW}	Address setup to write end	7	_	ns		
t _{HA}	Address hold from write end	0	_	ns		
t _{SA}	Address setup to write start	0	_	ns		
t _{PWE}	WE pulse width	7	_	ns		
t _{SD}	Data setup to write end	5	_	ns		
t _{HD}	Data hold from write end	0	_	ns		
t _{LZWE}	WE HIGH to low impedance ^[12, 13]	3	_	ns		
t _{HZWE}	WE LOW to HI-Z ^[12, 13]	-	5	ns		
t _{BW}	Byte Enable to write end	7	_	ns		

^{10.} Test conditions assume a signal transition time (rise/fall) of 3 ns or less, timing reference levels of 1.5 V (for V_{CC} ≥ 3 V) and V_{CC}/2 (for V_{CC} < 3 V), and input pulse levels of 0 to 3 V (for V_{CC} ≥ 3 V) and 0 to V_{CC} (for V_{CC} < 3 V). Test conditions for the read cycle use output loading shown in part (a) of Figure 3 on page 5, unless specified otherwise.

11. For all dual chip enable devices, CE is the logical combination of CE₁ and CE₂. When CE₁ is LOW and CE₂ is HIGH, CE is LOW; when CE₁ is HIGH or CE₂ is LOW, CE is HIGH.

^{12.} t_{HZOE}, t_{HZUE}, t_{HZWE}, t_{HZWE}, t_{LZOE}, t_{LZWE}, and t_{LZBE} are specified with a load capacitance of 5 pF as in (b) of Figure 3 on page 5. Transition is measured ±200 mV from steady state voltage.

^{13.} These parameters are guaranteed by design and are not tested.

^{14.} The internal write time of the memory is defined by the overlap of WE = V_{IL}, CE = V_{IL} and BHE or BLE = V_{IL}. These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates

^{15.} The minimum write cycle pulse width for Write Cycle No. 2 (WE Controlled, $\overline{\text{OE}}$ LOW) should be equal to sum of t_{ND} and t_{HZWE} .



Switching Waveforms

Figure 5. Read Cycle No. 1 of CY7C1041G (Address Transition Controlled) [16, 17]

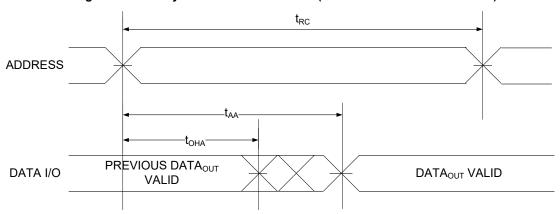
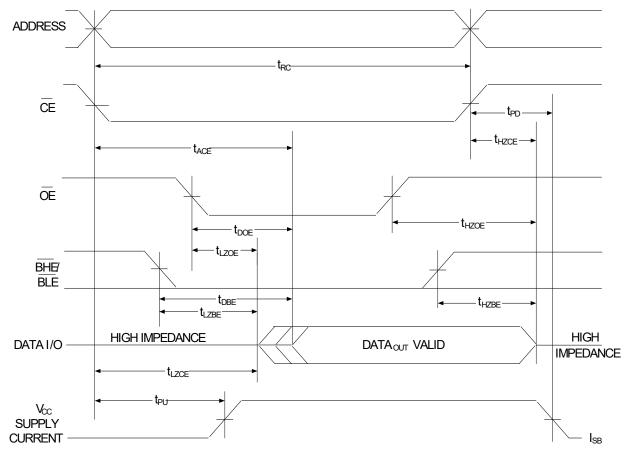


Figure 6. Read Cycle No. 2 (OE Controlled) [17]



^{16.} The device is continuously selected, $\overline{OE} = V_{|L}$, $\overline{CE} = V_{|L}$, \overline{BHE} or \overline{BLE} or both = $V_{|L}$. 17. \overline{WE} is HIGH for read cycle.



Switching Waveforms (continued)

Figure 7. Write Cycle No. 1 (CE Controlled) [18, 19, 20]

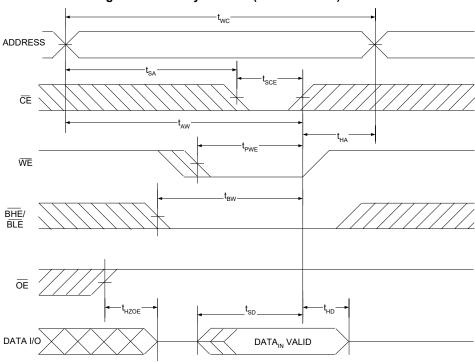
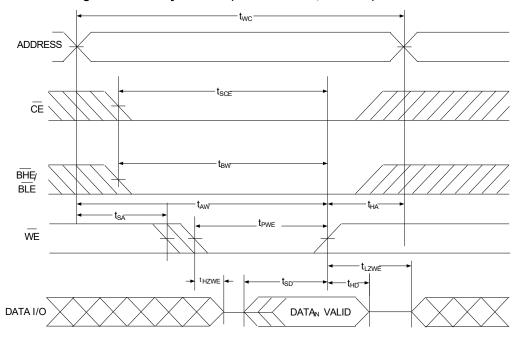


Figure 8. Write Cycle No. 2 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW) [18, 19, 20, 21]



- 18. Address valid prior to or coincident with CE LOW transition.

 19. The internal write time of the memory is defined by the overlap of WE = V_{IL}, CE = V_{IL} and BHE or BLE = V_{IL}. These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates
- 20. Data I/O is in HI-Z state if $\overline{CE} = V_{IH}$, or $\overline{OE} = V_{IH}$ or \overline{BHE} , and/or $\overline{BLE} = V_{IH}$.
- 21. The minimum write cycle pulse width should be equal to sum of t_{SD} and t_{HZWE}.

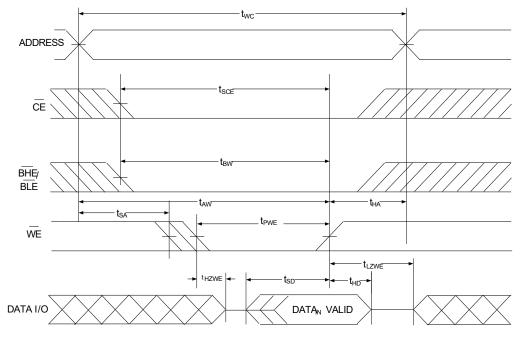


Switching Waveforms (continued)

 t_{WC} **ADDRESS** ĊĒ BHE/ BLE t_{HZWE} t_{HD} DATA_{IN} VALID

Figure 9. Write Cycle No. 3 (BLE or BHE Controlled) [22, 23]

Figure 10. Write Cycle No. 4 ($\overline{\text{WE}}$ Controlled) [22, 23, 24]



^{22.} The internal write time of the memory is defined by the overlap of WE = V_{IL}, \(\overline{CE} = V_{IL}\) and \(\overline{BHE}\) or \(\overline{BLE} = V_{IL}\). These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.

^{23.} Data I/O is in HI-Z state if $\overline{CE} = V_{IH}$, or $\overline{OE} = V_{IH}$ or \overline{BHE} , and/or $\overline{BLE} = V_{IH}$. 24. Data I/O is high impedance if $\overline{OE} = V_{IH}$.

^{25.} During this period the I/Os are in output state. Do not apply input signals.



Truth Table

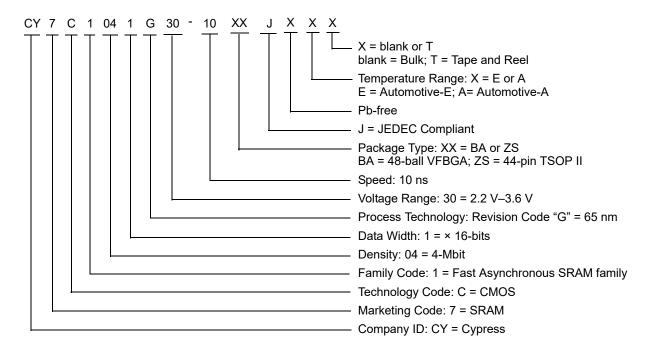
CE	OE	WE	BLE	BHE	I/O ₀ –I/O ₇	I/O ₈ -I/O ₁₅	Mode	Power
Н	Х	Х	Х	Х	HI-Z	HI-Z	Power down	Standby (I _{SB})
L	L	Н	L	L	Data out	Data out	Read all bits	Active (I _{CC})
L	L	Н	L	Н	Data out	HI-Z	Read lower bits only	Active (I _{CC})
L	L	Н	Н	L	HI-Z	Data out	Read upper bits only	Active (I _{CC})
L	Х	L	L	L	Data in	Data in	Write all bits	Active (I _{CC})
L	Х	L	L	Н	Data in	HI-Z	Write lower bits only	Active (I _{CC})
L	Х	L	Н	L	HI-Z	Data in	Write upper bits only	Active (I _{CC})
L	Н	Н	Х	Х	HI-Z	HI-Z	Selected, outputs disabled	Active (I _{CC})



Ordering Information

Speed (ns)	Voltage Range	Ordering Code	Package Diagram	Package Type (all Pb-free)	Operating Range
10	2.2 V-3.6 V	CY7C1041G30-10BAJXE	001-85259	48-ball VFBGA	Automotive-E
		CY7C1041G30-10BAJXET	001-85259	48-ball VFBGA, Tape and Reel	
		CY7C1041G30-10ZSXE	51-85087	44-pin TSOP II	
		CY7C1041G30-10ZSXET	51-85087	44-pin TSOP II, Tape and Reel	
		CY7C1041G30-10ZSXA	51-85087	44-pin TSOP II	Automotive-A
		CY7C1041G30-10ZSXAT	51-85087	44-pin TSOP II, Tape and Reel	

Ordering Code Definitions





Package Diagrams

Figure 11. 48-ball VFBGA (6 × 8 × 1.2 mm) BA48M/BK48M (0.35 mm Ball Diameter) Package Outline, 001-85259

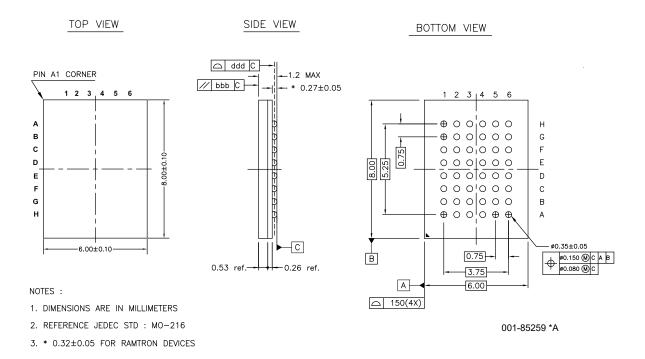
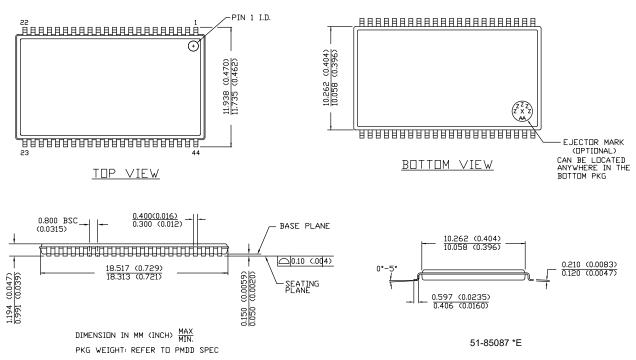


Figure 12. 44-pin TSOP Z44-II Package Outline, 51-85087





Acronyms

Table 1. Acronyms Used in this Document

Acronym	Description				
BHE	Byte High Enable				
BLE	Byte Low Enable				
CE	Chip Enable				
CMOS	Complementary Metal Oxide Semiconductor				
I/O	Input/Output				
OE	Output Enable				
SRAM	Static Random Access Memory				
TSOP	Thin Small Outline Package				
TTL	Transistor-Transistor Logic				
VFBGA	Very Fine-Pitch Ball Grid Array				
WE	Write Enable				

Document Conventions

Units of Measure

Table 2. Units of Measure

Symbol	Unit of Measure				
°C	degree Celsius				
MHz	megahertz				
μΑ	microampere				
μS	microsecond				
mA	milliampere				
mm	millimeter				
ns	nanosecond				
Ω	ohm				
%	percent				
pF	picofarad				
V	volt				
W	watt				



Document History Page

Oocument Title: CY7C1041G Automotive, 4-Mbit (256K words × 16-bit) Static RAM with Error-Correcting Code (ECC) Oocument Number: 001-91255				
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
*F	4996293	NILE	10/30/2015	Changed status from Preliminary to Final.
*G	5026902	NILE	11/25/2015	Added Automotive-A Temperature Range related information in all instances across the document. Updated Ordering Information: Updated part numbers.
*H	5427560	NILE	09/07/2016	Updated Maximum Ratings: Updated Note 5 (Replaced "2 ns" with "20 ns"). Updated DC Electrical Characteristics: Removed details of V _{OH} parameter corresponding to Test Condition "2.7 V to 3.6 V". Added details of V _{OH} parameter corresponding to Test Conditions "2.7 V to 3.0 V" and "3.0 V to 3.6 V". Updated Ordering Information: Updated part numbers. Updated to new template.
*	5787756	NILE	06/27/2017	Updated to new template. Completing Sunset Review.
*J	6249178	NILE	07/16/2018	Updated Features: Added "AEC-Q100 qualified". Added Note 2 and referred the same note in "Embedded ECC for single-bit error correction". Updated to new template. Completing Sunset Review.



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Document Number: 001-91255 Rev. *J Revised July 16, 2018 Page 16 of 16

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